

AMENDMENTS TO THE SPECIFICATION

Please replace Paragraph [0007] with the following paragraph rewritten in amendment format:

[0007] In other features, the first source and the first drain include n^+ regions and the body includes a p^+ region. The first body tapers as a distance between a midportion of the first body and the first gate decreases. The first body has at least one of a diamond shape, a circular shape, an elliptical shape, a hexagon shape, an octagon shape and a football shape. The first body ~~is in contact with~~overlaps the first gate or is spaced from the first gate in plan view.

Please replace Paragraph [0015] with the following paragraphs rewritten in amendment format:

[0015] FIG. 5A is a first exemplary layout of transistors including a body that is arranged in the source;

[0015.1] FIG. 5B is a second exemplary layout of transistors including a body that is arranged in the source and that overlaps the gate in plan view;

Please replace Paragraphs [0021] and [0022] with the following paragraph rewritten in amendment format:

[0021] Referring now to FIGs. 5A and 5B, a transistor 50 according to the present invention is shown to include one or more sources 54 and one or more drains 56. The sources 54 and the drains 56 include n^+ regions. While an NMOS transistor is shown, skilled artisans will appreciate that the present invention also applies to other

types of transistors such as PMOS transistors. Gates 58 are located between adjacent pairs of sources 54 and drains 56. In one implementation, the gates 58 that are located on opposite sides of the sources 54 are connected together as shown at 64. In other configurations, however, the gates 58 need not be connected together.

[0022] A body 66 including a p^+ region is arranged inside of and is surrounded by the source 54. The body 66 preferably has a shape that tapers as a distance between a midportion of the body 66 and adjacent gates decreases. The body 66 ~~may touch or not touch the~~ may overlap or be spaced from the gates 58 in the plan views of FIGs. 5A and 5B. ~~In other words, opposite edges of the body 66 electrically contact the gates 58 or are spaced from and not in electrical contact with the gates 58.~~ By utilizing some of the area of the source 54 for the body 66, the overall size of the transistor 50 is reduced as compared to conventional transistors. In the exemplary implementation that is shown in FIGs. 5A and 5B, the body 66 has a diamond shape.